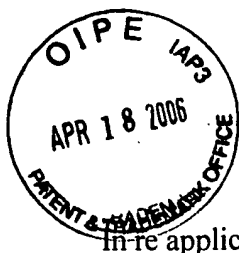


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IFW



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q89627

Koichi TERASHIMA, et al.

Appln. No.: 10/544,783

Group Art Unit: 1722

Confirmation No.: 5339

Examiner: Not Yet Assigned

Filed: August 08, 2005

For: METHOD FOR FORMING NICKEL SILICIDE FILM, METHOD FOR  
MANUFACTURING SEMICONDUCTOR DEVICE, AND METHOD FOR ETCHING  
NICKEL SILICIDE

SUBMISSION OF INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

For the Examiner's convenience, enclosed herewith is a copy of the English translation of the International Preliminary Report on Patentability (IPRP). It is assumed that copies of the cited references as required by §371(c) will be supplied directly by the International Bureau, but if further copies are needed, the undersigned will undertake to provide them upon request.

Respectfully submitted,

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WASHINGTON OFFICE

23373

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Date: April 18, 2006